THIN FILM TRANSISTOR, SEMICONDUCTOR DEVICE, AND METHOD FOR MANUFACTURING THE SAME

ABSTRACT OF THE DISCLOSURE

A semiconductor element is operated without being affected even when the substrate is largely affected by heat shrink such as a large substrate. Furthermore, a thin film semiconductor circuit and a thin film semiconductor device each having the semiconductor element. Also, a semiconductor element is operated without being affected even if there is slight mask deviation. In view of them, a plurality of gate electrodes formed so as to overlap a lower concentration impurity region of a semiconductor layer than drain regions on a drain region side. Also, source regions and the drain regions corresponding to the respective gate electrodes are formed so that current flows in opposite directions each other through channel regions corresponding to the gate electrodes. Further, the number of the channel regions in which a current flows in a first direction is equal to the number of the channel regions in which a current flows in a direction opposite to the first direction.

(Fig. 1A)